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DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

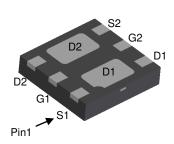
Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
001/	50mΩ @V _{GS} = -4.5V	-4.5A
-20V	100mΩ @V _{GS} = -2.5V	-3.2A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors



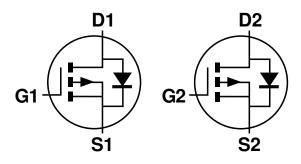
Bottom View

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: U-DFN2020-6 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208[®]
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2065UFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMP2065UFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



P5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	201	5	2016		2017	20	18	2019		2020	2	2021
Code	С		D		E		=	G		Н		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V _{DSS}	-20	V	
Gate-Source Voltage		V _{GSS}	±12	V	
Continuous Drain Current (Note 6) V _{GS} = -4.5V	l _D	-4.5 -3.6	Α		
Pulsed Drain Current (10µs pulse, duty cycle = 1	%)		I _{DM}	-25	Α
Maximum Continuous Body Diode Forward Curre	ent (Note 6)		Is	-1.4	Α
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	-13	Α
Avalanche Energy (Note 7) L = 0.1mH		Eas	9	mJ	

Thermal Characteristics

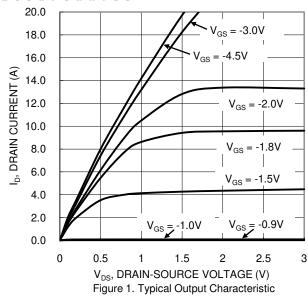
Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.74	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	0	171	°C/W
Thermal nesistance, Junction to Ambient (Note 3)	t<10s	$R_{\theta JA}$	131	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P _D	1.54	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	D	82	°C/W
Thermal nesistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	60	
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	13		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

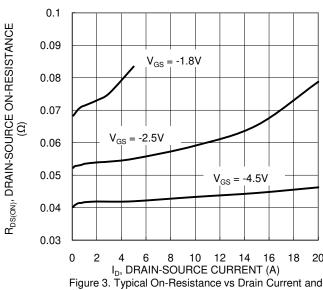
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$		
Zero Gate Voltage Drain Current $T_J = +25$ °C	I _{DSS}	_	_	-1.0	μΑ	$V_{DS} = -20V, V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)	ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	-0.4	_	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$		
			40	50		$V_{GS} = -4.5V, I_D = -2.0A$		
Static Drain-Source On-Resistance	D		55	100	mΩ	$V_{GS} = -2.5V, I_D = -2.0A$		
Static Diani-Source On-Hesistance	R _{DS(ON)}	_	75	150	11122	$V_{GS} = -1.8V, I_D = -1.6A$		
			95	200		$V_{GS} = -1.5V, I_D = -1.0A$		
Diode Forward Voltage	V_{SD}	_	-0.75	-1.1	V	$V_{GS} = 0V, I_{S} = -1A$		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	Ciss	_	752	_	pF	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		
Output Capacitance	Coss	_	87	_	рF	$V_{DS} = -15V, V_{GS} = 0V$ -f = 1.0MHz		
Reverse Transfer Capacitance	C_{rss}	_	78	_	pF	1 = 1.01VII 12		
Gate Resistance	R_{G}	_	15.2	_	Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$		
Total Gate Charge	Q_{g}		9.1		nC	V 45V V 4V		
Gate-Source Charge	Qgs		1.2	_	nC	$V_{GS} = -4.5V, V_{DS} = -4V,$ $I_{D} = -3.5A$		
Gate-Drain Charge	Q_{gd}		1.9		nC	ID = -3.5A		
Turn-On Delay Time			5.4	_	ns			
Turn-On Rise Time		_	8.3	_	ns	$V_{DS} = -4V, V_{GS} = -4.5V,$		
Turn-Off Delay Time			47	_	ns	$R_G = 6\Omega$, $I_D = -1A$		
Turn-Off Fall Time	t _F	_	20	_	ns			

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

DMP2065UFDB





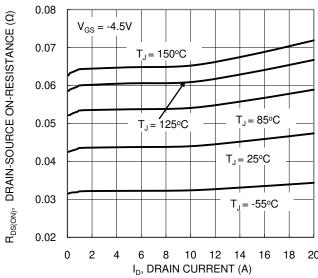


Figure 5. Typical On-Resistance vs Drain Current and Junction Temperature

Gate Voltage

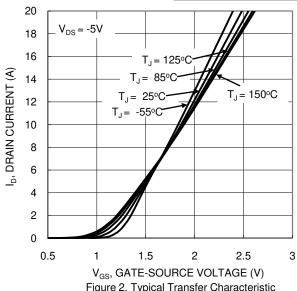
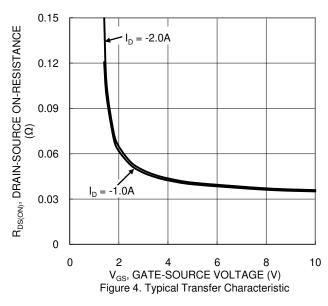


Figure 2. Typical Transfer Characteristic



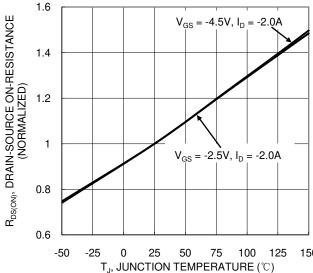
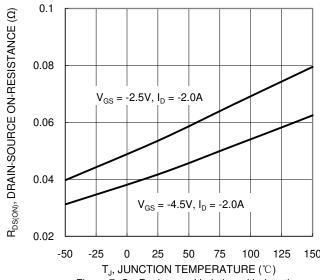


Figure 6. On-Resistance Variation with Junction Temperature



DMP2065UFDB

 $I_D = -1mA$



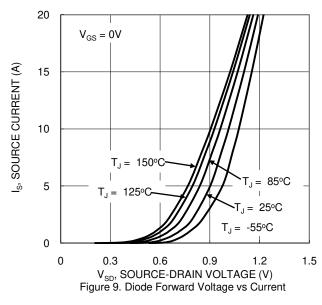
 $V_{\mathrm{GS(TH)}},$ GATE THRESHOLD VOLTAGE (V) 0.6 $I_D = -250 \mu A$ 0.4 0.2 0 50 100 -50 -25 25 75 125 150 T_J, JUNCTION TEMPERATURE (°C)

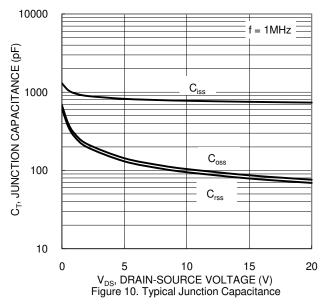
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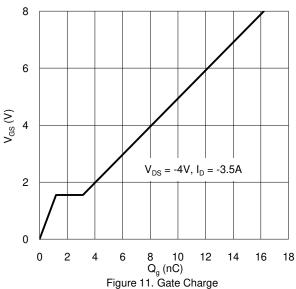
8.0

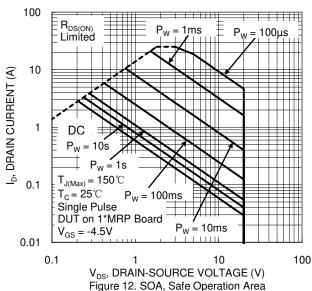
Figure 7. On-Resistance Variation with Junction Temperature

Figure 8. Gate Threshold Variation vs Junction Temperature











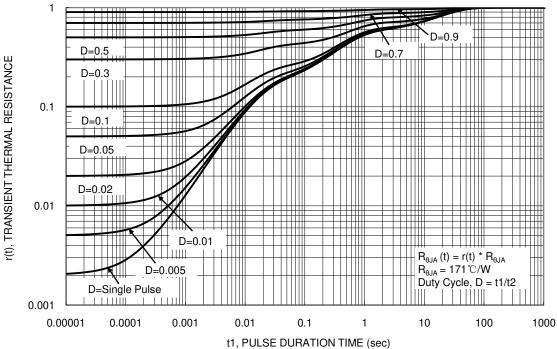


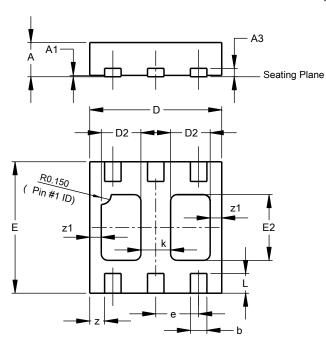
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

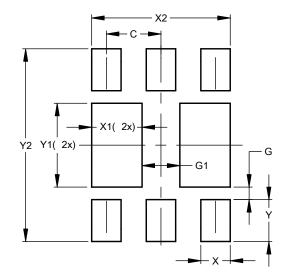


U-DFN2020-6 Type B						
Dim	Min	Max	Тур			
Α	0.545	0.605	0.575			
A1	0.00	0.05	0.02			
А3	-	-	0.13			
Ь	0.20	0.30	0.25			
D	1.95	2.075	2.00			
D2	0.50	0.70	0.60			
е	-	-	0.65			
Е	1.95	2.075	2.00			
E2	0.90	1.10	1.00			
k	1	1	0.45			
L	0.25	0.35	0.30			
Z	-	-	0.225			
z1	-	-	0.175			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value
Dilliensions	(in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Υ	0.500
Y1	1.000
Y2	2.300



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